



# microSD3.0 UHS-I Specification

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## Revision History:

<b>Rev.</b>	<b>Date</b>	<b>Changes</b>	<b>Remark</b>
1.0	2017/12/16	Basic spec and architecture	Preliminary



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## 1. Overview

### 1.1 Product Description

The microSD3.0 Cards are fully compatible with Physical Layer Specification, Version 3.0 (this specification is available from the SDA), support Ultra High Speed(UHS), provides high write/read speed and high IOPS, It was designed to meet the security, high capacity, high performance and environmental requirements inherent in next generation consumer electronic devices.

The SD card system is a new mass-storage system based on innovations in semiconductor technology. It has been developed to provide an inexpensive, mechanically robust storage medium in card form for multimedia consumer applications. SD card allows the design of inexpensive players and drivers without moving parts. A low power consumption and a wide supply voltage range favors consumer electronic devices.

Ultra High Speed (UHS) Card

It provides up to 104MB/s\* performance. UHS cards are backward compatible on non-UHS hosts.

\*Based on internal testing; performance may vary depending upon host device.

1 megabyte (MB) =1,000,000bytes.

### 1.2 Features Summary

-Capacity: 4GB/8GB/16GB/32GB/64GB

-Complies to SD specifications version 3.0

-Voltage operating: 2.7~3.6V.

-Targeted for portable and stationary applications

-Greater Performance Choices

-Bus Speed Mode:

DS-Default Speed mode: 3.3V signaling, frequency up to 25MHz, up to 12.5MB/sec

HS-High Speed mode: 3.3V signaling, frequency up to 50MHz, up to 25MB/sec

SDR12-1.8V signaling, frequency up to 25MHz, up to 12.5MB/sec

SDR25-1.8V signaling, frequency up to 50MHz, up to 25MB/sec

SDR50-1.8V signaling, frequency up to 100MHz, up to 50MB/sec

SDR104-1.8V signaling, frequency up to 208MHz, up to 104MB/sec

DDR50-1.8V signaling, frequency up to 50MHz, sampled on both clock edges, up to 50MB/s

-Switch function command supports Bus Speed Mode, Command System, Drive Strength, and future functions.

-password protection (CMD42-LOCK\_UNLOCK)

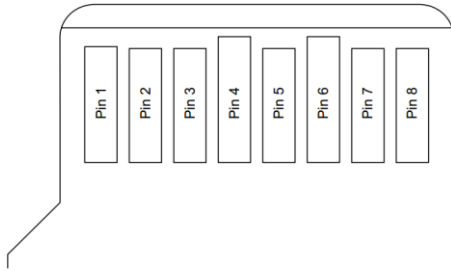
-Sophisticated system for error recovery including a powerful ECC

-Global Wear Leveling

-Power management for low power operation

-Add TF card adapter can be used in SD card socket

## 2. Pin Assignment



Pin No.	SD Mode			SPI Mode		
	Name	Type	Description	Name	Type	Description
1	Dat2	I/O/PP	Data Line [Bit 2]	RSV		Reserved
2	CD/DAT3	I/O/PP	Card Detect / Data Line [Bit 3]	CS	I	Chip Select
3	CMD	PP	Command/Response	DI	I	Data In
4	VDD	S	Supply voltage	VDD	S	Supply voltage
5	CLK	I	Clock	SCLK	I	Clock
6	VSS	S	Supply voltage ground	VSS	S	Supply voltage ground
7	DAT0	I/O/PP	Data Line [Bit 0]	DO	O/PP	Data Out
8	DAT1	I/O/PP	Data Line [Bit 1]	RSV		Reserved

S: power supply; I: input; O: output; PP: I/O using push-pull drivers

**Table 1: Pin Assignment**



### 3. Product List

Part Number	Capacity	Actual Size	Speed Class (Note1)	UHS-I (Note1)	Type
SDSDQAB-004G-MK	4GB	3.62GB	C10,U1,V10	SDR104	SDHC
SDSDQAB-008G-MK	8GB	7.68GB	C10,U1,V10	SDR104	SDHC
SDSDQAD-016G-MK	16GB	14.75GB	C10,U1,V10,A2	SDR104	SDHC
SDSDQAD-032G-MK	32GB	29.12GB	C10,U1,V10,A2	SDR104	SDHC
SDSDQAD-064G-MK	64GB	58.24GB	C10,U1,V10,A2	SDR104	SDHC

**Table 2: Product List**

**Note1:** \*Measurement based on VTE3100 Test Matrix device, SW 3.2A software or up version.

Test scripts:

SD\_Card(Spec3.0\_High&Extended-Capacity\_UHS-I and Non-UHS-I)\_Compliance [rev31R].vte

SDR104@SDR104-208MHz.

SD\_Card (Spec2.0-3.0 High&Extended-Capacity\_UHS-I) Performance-Speed (Multiple Block Sequential) [rev31M] - SDR104-With Background Data.vte]

*\*Maximum speed differs from the bus I/F speed. It varies depending upon the card performance. The average speed that a device writes to an SD memory card may vary depending upon the device and the operation it is performing. Normal and high-speed cards can also be used with UHS-I host devices, but the high performance enabled by a UHS-I host device can only be achieved with a UHS- I memory card.*



## 4. Current Consumption

Standby current: 500uA (Maximum value)

Standby current: 250uA (average value)

Operating current: 250mA (Maximum value)

Operating current: 150mA (average value)

\*Test condition: Realtek5308 card reader (Voltage 3.3V), Fluke289C multi-meter.

## 5. Reliability and Durability

<b>Temperature</b>	Operation: -25°C/85°C Storage: -25°C/85°C
<b>Moisture and corrosion</b>	Operation: 25°C/95% rel. humidity Storage: 40°C/93% rel. hum./500h Salt Water Spray: 3% NaCl/35C; 24h acc. MIL STD Method 1009
<b>Durability</b>	10,000 insertion/removal cycles;
<b>Bending</b>	10[N] Center 200[mm/minute] 60[sec]
<b>Torque</b>	0.10Nm, +/-2.5 deg.max.
<b>Drop test</b>	1.5m free fall
<b>Electrostatic Discharge (ESD)</b>	IEC 61000-4-2 contact discharge: +/- 2[kV] and +/- 4[kV] 150[pF],330[Ohm] air discharge: up to +/- 15[kV] 150[pF], 330[Ohm]

**Table 3: Reliability and Durability**

## 6. SD Card Registers

### 6.1 Card Identification Register (CID)

The Card Identification (CID) register is 128 bit wide. It contains the card identification information used during the card identification phase. Every individual flash card shall have a unique identification number.

The structure of the CID register is defined in the following table.

<b>CID Bit</b>	<b>Width</b>	<b>Name</b>	<b>Field</b>
[127:120]	8	Manufacture ID	MID
[119:104]	16	OEM/Application ID	OID
[103:64]	40	Product Name	PNM
[63:56]	8	Product Revision	PRV
[55:24]	32	Product Serial Number	PSN
[23:20]	4	Reserved	---
[19:8]	12	Manufacturing Date	MDT
[7:1]	7	CRC7 check sum	CRC
[0]	1	Not used,always"1	---

**Table 4: SD Card CID Table**

- All contents in the CID table are programmable; Manufacturers can update the CID data through utility.
- Manufacturers should license MID and OID field form the SD Card Association(SDA)



## 6.2 Card Specific Data Register (CSD)

The Card-Specific Data register provides information regarding access to the card contents. The CSD defines the data format, error correction type, maximum data access time, whether the DSR register can be used, etc. The programmable part of the register (entries marked by W or E, see below) can be changed by CMD27. The CSD Table Version 2.0(as shown below) is applied to SDHC and SDXC Cards. Note that bits [15:0] are programmable by the host side. Refer to the SD specification for detailed information

CSD Bit	Width	Name	Field	Value	Note
[127:126]	2	CSD structure	CSD_STRUCTURE	01b	V2.0(>2G B Card)
[125:120]	6	Reserved	---	---	---
[119:112]	8	Data read access-time 1	(TAAC)	0E h	
[111:104]	8	Data read access-time2 in CLK cycles(NSA*100)	(NSAC)	00 h	
[103:96]	8	Max data transfer rate	(TRAN_SPEED)	32 h 5A h 0B h 2B h	
[95:84]	12	Card command classes	CCC	5B5 h	
[83:80]	4	Max. read data block length	(READ_BLK_LEN)	9 h	512 Byte
[79]	1	Partial block read allowed	(READ_BLK_PARTIAL)	0	
[78]	1	Write block misalignment	(WRITE_BLK_MISALIGN)	0	
[77]	1	Read block misalignment	(READ_BLK_MISALIGN)	0	
[76]	1	DSR implemented	DSR_IMP	x	
[75:70]	6	Reserve	---	---	
[69:48]	22	Device size	C_SIZE	xxxxxxh	
[47]	1	Reserved	---	0	
[46]	1	Erase single block enable	(ERASE_BLK_EN)	1	
[45:39]	7	Erase sector size	(SECTOR_SIZE)	7F h	
[38:32]	7	Write protect group size	C_SIZE	0 b	
[31]	1	Write protect group enable	---	0	
[30:29]	2	Reserved	(ERASE_BLK_EN)	0 b	
[28:26]	3	Write speed factor	(SECTOR_SIZE)	010 b	
[25:22]	4	Max. write data block length	(WP_GRP_SIZE)	9 h	
[21]	1	Partial block write allowed	(WP_GRP_ENABLE)	0	
[20:16]	5	Reserved	---	---	
[15]	1	File format group	(FILE_FORMAT_GRP)	0	
[14]	1	Copy flag	COPY	x	
[13]	1	Permanent write protection	PERM_WRITE_PROTECT	x	
[12]	1	Temporary write protection	TMP_WRITE_PROTECT	x	
[11:10]	2	File format	(FILE_FORMAT)	00 b	
[9:8]	2	Reserved	---	00 b	
[7:1]	7	CRC	CRC	---	
[0]	1	Not used,always'1'	---	1	



**Table 5: CSD (Version 2.0) Table**

## 7. Bus Operation Conditions

### 7.1 For 3.3V Signaling

#### 7.1.1 Threshold Level for High Voltage Range

Parameter	Symbol	Min	Max	Unit	Remark
Supply Voltage	V <sub>DD</sub>	2.7	3.6	V	
Output High Voltage	V <sub>OH</sub>	0.75* V <sub>DD</sub>		V	I <sub>OH</sub> =2mA V <sub>DD min</sub>
Output Low Voltage	V <sub>OL</sub>		0.125* V <sub>DD</sub>	V	I <sub>OL</sub> =2mA V <sub>DD min</sub>
Input High Voltage	V <sub>IH</sub>	0.625* V <sub>DD</sub>	V <sub>SS</sub> +0.3	V	
Input Low Voltage	V <sub>IL</sub>	V <sub>SS</sub> -0.3	0.25* V <sub>DD</sub>	V	
Power Up Time			250	ms	From 0V to V <sub>DD min</sub>

**Table 6: Threshold Level for High Voltage**

#### 7.1.2 Peak Voltage and Leakage Current

Parameter	Symbol	Min	Max	Unit	Remark
Peak voltage on all lines		-0.3	V <sub>DD</sub> +0.3	V	
All Inputs					
Input Leakage Current		-10	10	uA	
All Outputs					
Output Leakage Current		-10	10	uA	

**Table 7: Peak Voltage and Leakage Current**

#### 7.1.3 Bus Signal Line Load

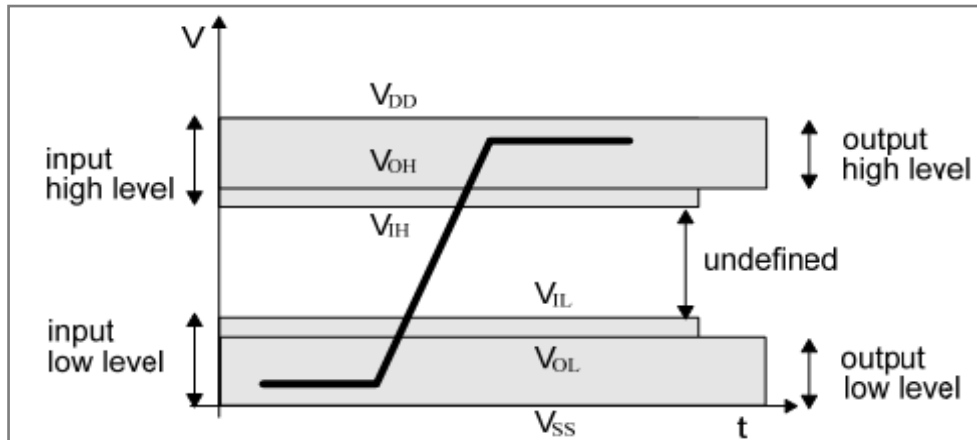
Parameter	Symbol	Min	Max	Unit	Remark
Pull-up resistance	R <sub>CMD</sub> R <sub>DAT</sub>	10	100	K $\Omega$	To prevent bus floating
Total bus capacitance for each signal line	C <sub>L</sub>		40	pF	1 card C <sub>HOST</sub> +C <sub>BUS</sub> shall not exceed 30pF
Card capacitance for each signal pin	C <sub>CARD</sub>		10	pF	
Maximum signal inductance			16	nH	
Pull-up resistance inside card(pin1)	R <sub>DAT3</sub>	10	90	K $\Omega$	May be used for card detection
Capacity Connected to Power Line	C <sub>C</sub>		5	uF	To prevent inrush current

**Table 8: Bus Operating Conditions - Signal Line's Load**



### 7.1.4 Bus Signal Levels

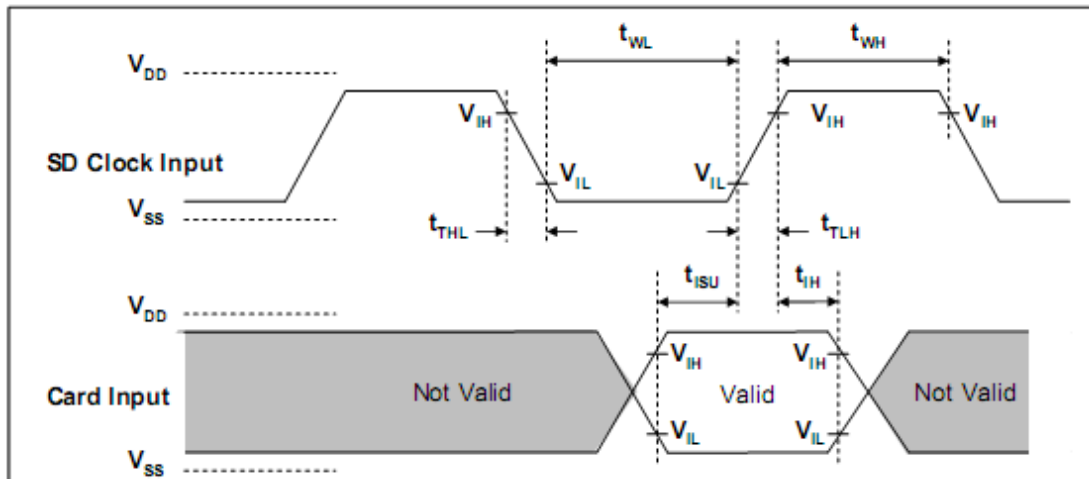
As the bus can be supplied with a variable supply voltage, all signal levels are related to the supply voltage.



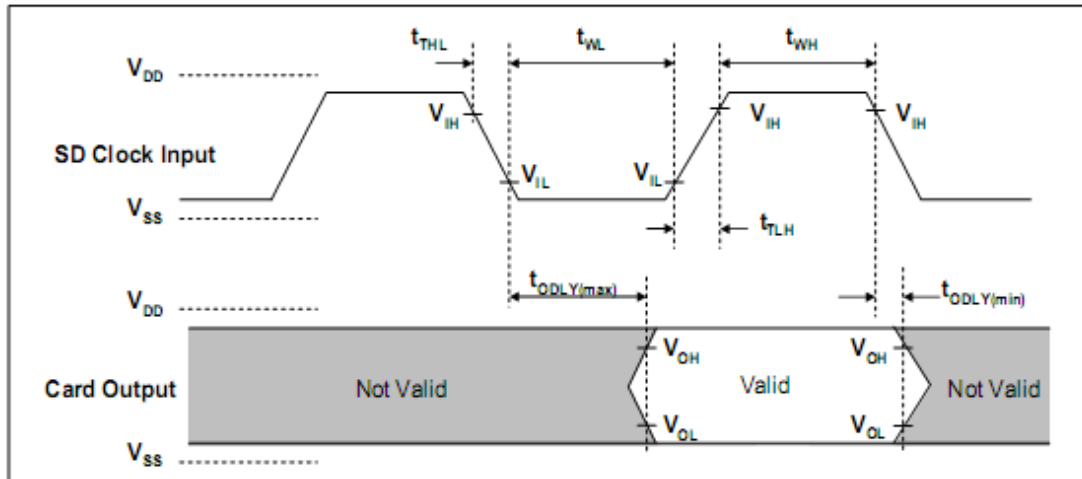
**Figure 1: Bus Signal Levels**

To meet the requirements of the JEDEC specification JESD8-1A and JESD8-7, the card input and output voltages shall be within the specified ranges shown in Table 6-2 for any VDD of the allowed voltage range:

### 7.1.5 Bus Timing (Default)



**Figure 2: Card input Timing (Default Speed Card)**



**Figure 3: Card Output Timing (Default Speed Mode)**

(1) 0 Hz means to stop the clock. The given minimum frequency range is for cases where continues

Parameter	Symbol	Min.	Max	Unit	Remark
<b>Clock CLK</b> (All values are referred to min ( $V_{IH}$ ) and max ( $V_{IL}$ ))					
Clock frequency data transfer Mode	f <sub>pp</sub>	0	25	MHz	C <sub>CARD</sub> ≤ 10pF (1 card)
Clock frequency Identification Mode	f <sub>OD</sub>	0 <sup>(1)</sup> /100	400	KHz	C <sub>CARD</sub> ≤ 10pF (1 card)
Clock low time	t <sub>WL</sub>	10		ns	C <sub>CARD</sub> ≤ 10pF (1 card)
Clock high time	t <sub>WH</sub>	10		ns	C <sub>CARD</sub> ≤ 10pF (1 card)
Clock rise time	t <sub>TLH</sub>		10	ns	C <sub>CARD</sub> ≤ 10pF (1 card)
Clock fall time	t <sub>THL</sub>		10	ns	C <sub>CARD</sub> ≤ 10pF (1 card)
<b>Inputs CMD, DAT</b> (referenced to CLK)					
Input set-up time	t <sub>ISU</sub>	5		ns	C <sub>CARD</sub> ≤ 10pF (1 card)
Input hold time	t <sub>IH</sub>	5		ns	C <sub>CARD</sub> ≤ 10pF (1 card)
<b>Outputs CMD, DAT</b> (referenced to CLK)					
Output Delay time during Data Transfer Mode	t <sub>ODLY</sub>	0	14	ns	C <sub>L</sub> ≤ 40pF (1 card)
Output Hold time	t <sub>OH</sub>	0	50	ns	C <sub>L</sub> ≤ 40pF (1 card)

clock is required (refer to Chapter 4.4-Clock Control)

**Table 9: Bus Timing-Parameters Values (Default Speed)**

### 7.1.6 Bus Timing (High-Speed Mode)

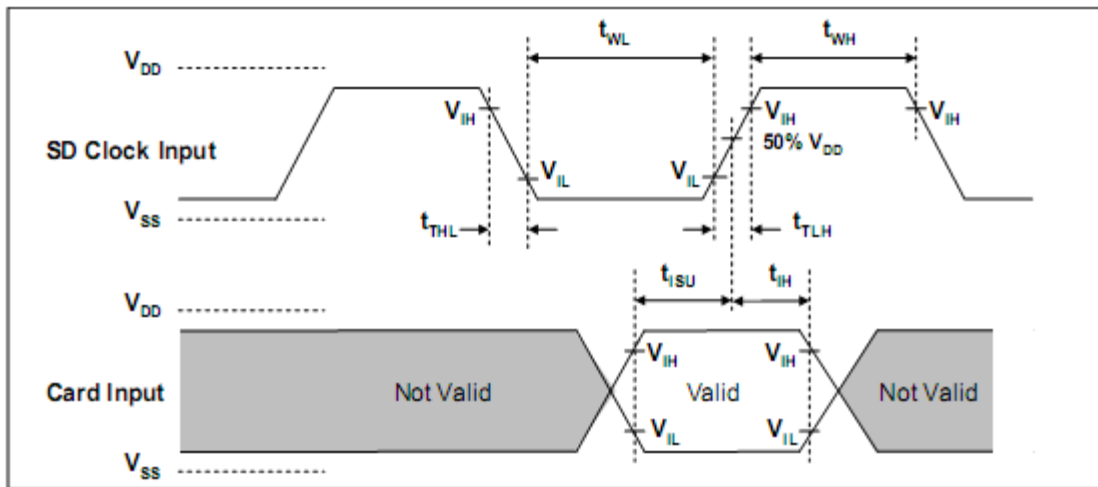


Figure 4: Card Input Timing (High Speed Card)

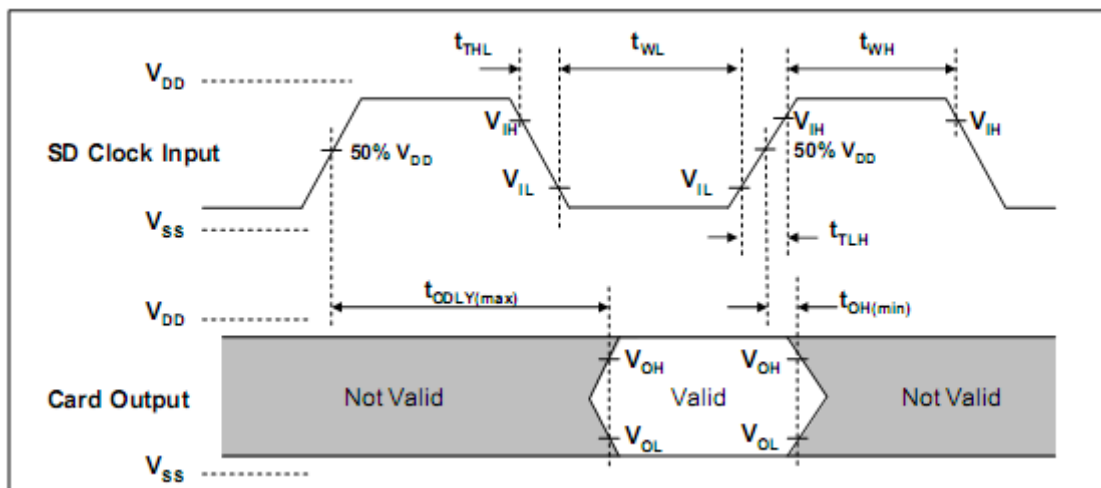


Figure 5: Card Output Timing (High Speed Mode)

Parameter	Symbol	Min.	Max	Unit	Remark
<b>Clock CLK</b> (All values are referred to min ( $V_{IH}$ ) and max ( $V_{IL}$ ))					
Clock frequency data transfer Mode	fpp	0	50	MHz	$C_{CARD} \leq 10\text{pF}$ (1 card)
Clock low time	$t_{WL}$	7		ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
Clock high time	$t_{WH}$	7		ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
Clock rise time	$t_{TLH}$		3	ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
Clock fall time	$t_{THL}$		3	ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
<b>Inputs CMD, DAT</b> (referenced to CLK)					
Input set-up time	$t_{ISU}$	6		ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
Input hold time	$t_{IH}$	2		ns	$C_{CARD} \leq 10\text{pF}$ (1 card)
<b>Outputs CMD, DAT</b> (referenced to CLK)					



Output Delay time during Data Transfer Mode	$t_{ODLY}$		14	ns	$C_L \leq 40\text{pF}$ (1 card)
Output Hold time	$t_{OH}$	2.5		ns	$C_L \geq 15\text{pF}$ (1 card)
Total System capacitance for each line <sup>1P</sup>	$C_L$		40	pF	1 card

(1) In order to satisfy sever timing , host shall drive only one card.

**Table 10: Bus Timing – Parameters Values (High Speed)**

## 7.2 For 1.8V Signaling

### 7.2.1 Threshold Level for High Voltage Range

Parameter	Symbol	Min	Max	Unit	Remark
Supply Voltage	$V_{DD}$	2.7	3.6	V	
Regulator Voltage	$V_{DDIO}$	1.7	1.95	V	Generated by $V_{DD}$
Output High Voltage	$V_{OH}$	1.4		V	$I_{OH}=2\text{mA}$ $V_{DD \text{ min}}$
Output Low Voltage	$V_{OL}$		0.45	V	$I_{OL}=2\text{mA}$ $V_{DD \text{ min}}$
Input High Voltage	$V_{IH}$	1.27	2.0	V	
Input Low Voltage	$V_{IL}$	$V_{SS}-0.3$	0.58	V	

**Table 11: Threshold Level for High Voltage**

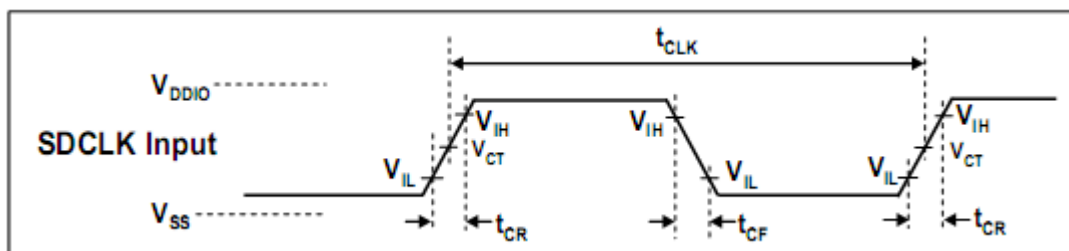
### 7.2.2 Peak Voltage and Leakage Current

Parameter	Symbol	Min	Max	Unit	Remark
Input Leakage Current		-2	2	uA	DAT3 pull-up is disconnected

**Table 12: Peak Voltage and Leakage Current**

### 7.2.3 Bus Timing Specification in SDR12, SDR25, SDR50 and SDR104 Modes

#### 7.2.3.1 Clock Timing



**Figure 6: Clock Signal Timing**

Symbol	Min	Max	Unit	Remark
$t_{CLK}$	4.8	-	ns	208MHz (Max.), Between rising edge, $V_{CT}=0.975V$
$t_{CR}, t_{CF}$	-	$0.2 * t_{CLK}$	ns	$t_{CR}, t_{CF} < 2.00\text{ns}$ (max.) at 208MHz, $CCARD=10\text{pF}$ $t_{CR}, t_{CF} < 2.00\text{ns}$ (max.) at 100MHz, $CCARD=10\text{pF}$ The absolute maximum value of $t_{CR}, t_{CF}$ is 10ns regardless of clock frequency.
Clock Duty	30	70	%	

**Table 13: Clock Signal Timing**

### 7.2.3.2 Card Input Timing

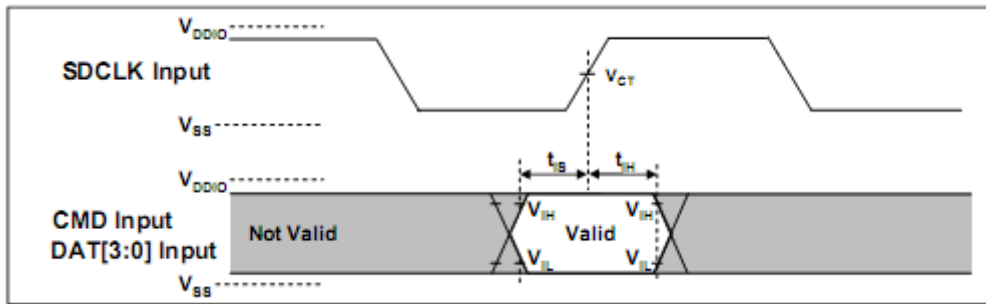


Figure 7: Card Input Timing

Symbol	Min	Max	Unit	SDR104 mode
$t_{IS}$	1.40	-	ns	$C_{CARD} = 10\text{pF}$ , $V_{CT} = 0.975\text{V}$
$t_{IH}$	0.80	-	ns	$C_{CARD} = 5\text{pF}$ , $V_{CT} = 0.975\text{V}$
Symbol	Min	Max	Unit	SDR12, SDR25 and SDR50 modes
$t_{IS}$	3.00	-	ns	$C_{CARD} = 10\text{pF}$ , $V_{CT} = 0.975\text{V}$
$t_{IH}$	0.80	-	ns	$C_{CARD} = 5\text{pF}$ , $V_{CT} = 0.975\text{V}$

Table 14: SDR50 and SDR104 Input Timing

### 7.2.3.3 Card Output Timing

#### 7.2.3.3.1 Output Timing of Fixed Data Window (SDR12, SDR25 and SDR50)

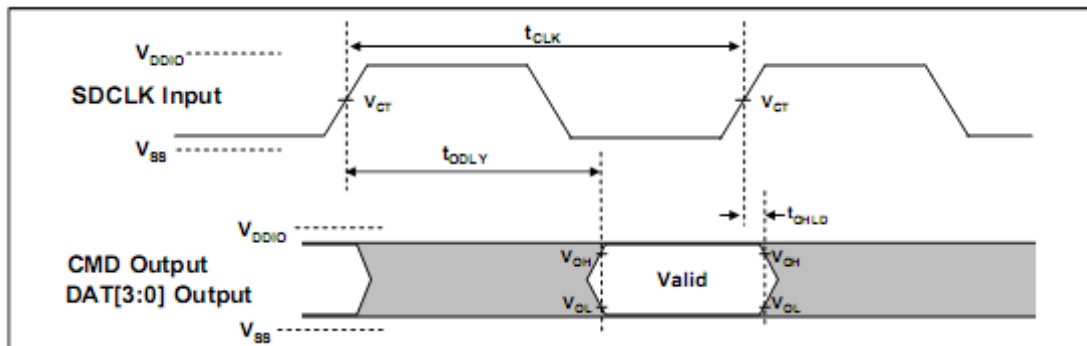
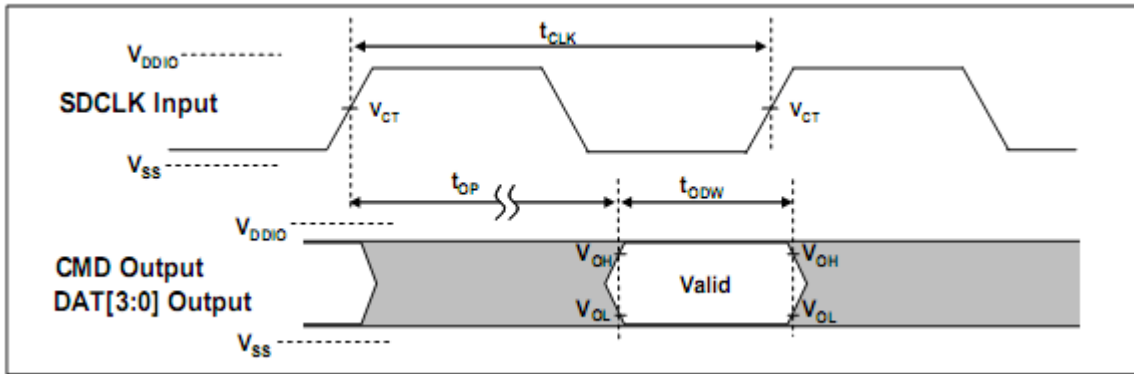


Figure 8: Output Timing of Fixed Data Window

Symbol	Min	Max	Unit	Remark
$t_{ODLY}$	-	7.5	ns	$t_{CLK} \geq 10.0\text{ns}$ , $CL=30\text{pF}$ , using driver Type B, for SDR50.
$t_{ODLY}$	-	14	ns	$t_{CLK} \geq 20.0\text{ns}$ , $CL=40\text{pF}$ , using driver Type B, for SDR25 and SDR12.
$t_{OH}$	1.5	-	ns	Hold time at the $t_{ODLY}$ (min.). $CL=15\text{pF}$

Table 15: Output Timing of Fixed Data Window

### 7.2.3.3.2 Output Timing of Variable Window (SDR104)



**Figure 9: Output Timing of Variable Data Window**

Symbol	Min	Max	Unit	Remark
$t_{OP}$	-	2	UI	Card Output Phase
$\Delta t_{OP}$	-350	+1550	ps	Delay variation due to temperature change after tuning
$t_{ODW}$	0.60	-	UI	$t_{ODW} = 2.88ns$ at 208MHz

**Table 16: Output Timing of Variable Data Window**

## 8. Physical Dimension

Type	Measurement
Length	15mm +/- 0.1mm(B)
Width	11mm +/- 0.1mm(A)
Thickness	1.0mm +/- 0.1mm(C)
	0.7mm +/- 0.1mm(C1)
Weight	0.33 gram Max

**Physical Dimension Specifications (Unit in mm)**



Mechanical form factor as follows: (Unit in mm)

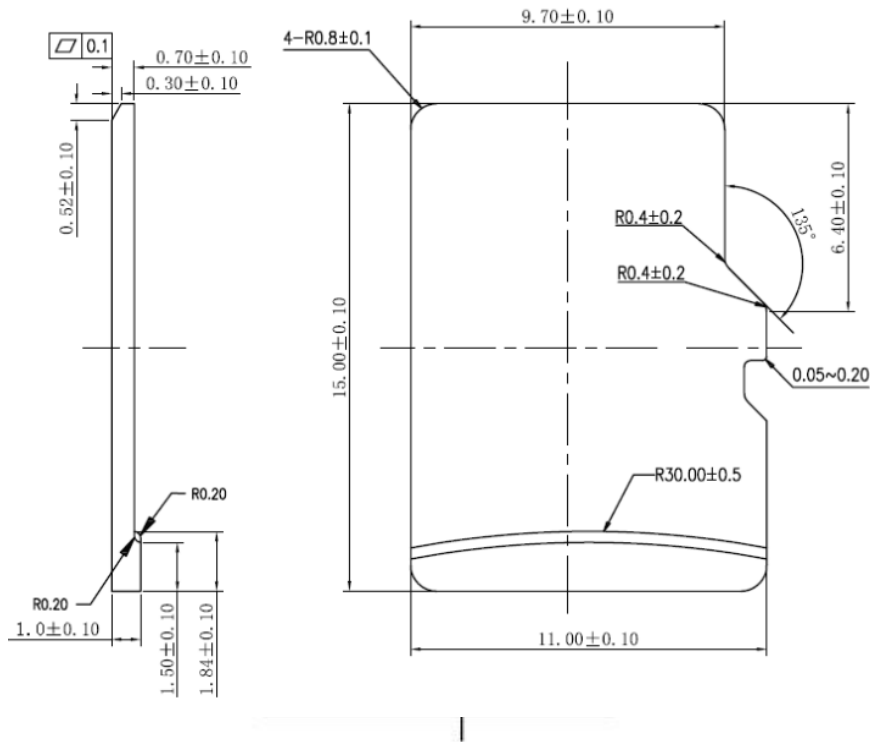


Figure 10: Dimension Drawing

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[U368-64GB](#) [U368-256GB](#) [FD4AU2666CWGSM](#) [FC5NE2128G-E](#) [U330-32GB](#) [FC5RC2008G-R](#) [T1-32G](#) [U210-64GB](#) [T1-64GB](#)  
[MKSD008G-CGT1](#) [SDSDQAB-008G-MK](#) [MKUS128G-CGT2](#) [MKUS064G-CGT1](#) [MKSD128G-CGT2](#)